NSN 5962-01-330-5530

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View Online at https://aerobasegroup.com/nsn/5962-01-330-5530

Overall Height:
Between 0.345 inches and 0.425 inches
Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
Between 0.150 inches and 0.210 inches
Maximum Power Dissipation Rating:
1.02 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and schottky and programmable and high impedance and w/active pull-up and 3-state output and electrostatic sensitive
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
13 input
Case Outline Source And Designator:
D-3 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Time Rating Per Chacteristic:
90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:

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N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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